

## N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
30	0.032 at V <sub>GS</sub> = 10 V	6.8	9.2 nC
	0.045 at V <sub>GS</sub> = 4.5 V	5.8	

### FEATURES

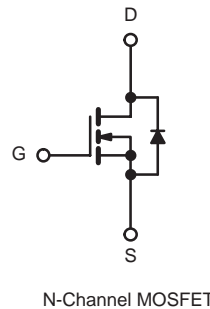
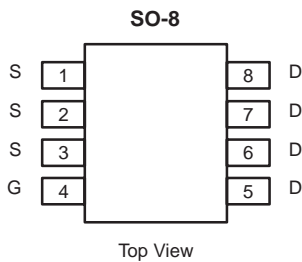
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

- Notebook Load Switch
- Low Current dc-to-dc



ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V <sub>DS</sub>	30	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 25 °C	I <sub>D</sub>	6.8 <sup>a</sup>	A
	T <sub>C</sub> = 70 °C		5 <sup>a</sup>	
	T <sub>A</sub> = 25 °C		6.5 <sup>b,c</sup>	
	T <sub>A</sub> = 70 °C		4.9 <sup>b,c</sup>	
Pulsed Drain Current		I <sub>DM</sub>	30	
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	I <sub>S</sub>	2.7	
	T <sub>A</sub> = 25 °C		1.7 <sup>b,c</sup>	
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	4.1	W
	T <sub>C</sub> = 70 °C		2.6	
	T <sub>A</sub> = 25 °C		2 <sup>b,c</sup>	
	T <sub>A</sub> = 70 °C		1.25 <sup>b,c</sup>	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	t ≤ 5 s	R <sub>thJA</sub>	45	62.5	°C/W
Maximum Junction-to-Foot	Steady State	R <sub>thJF</sub>	25	30	

Notes:

- Package Limited.
- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- Maximum under Steady State conditions is 110 °C/W.

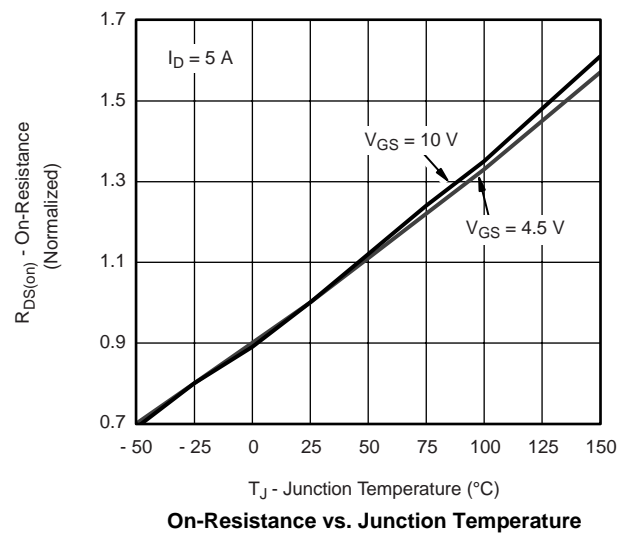
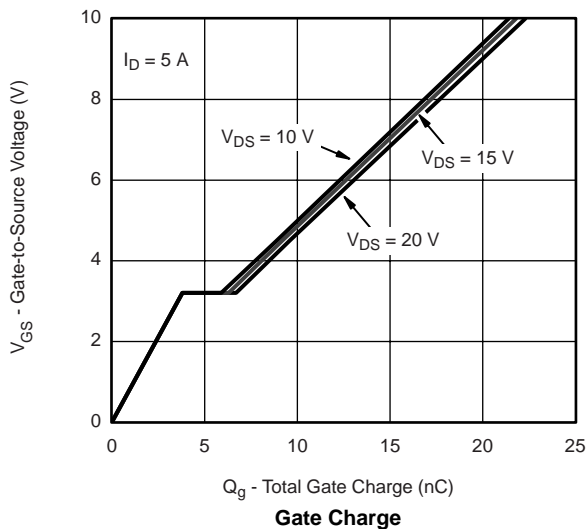
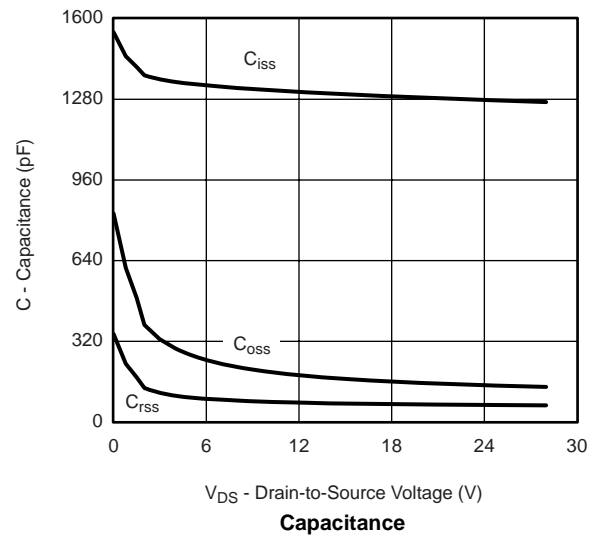
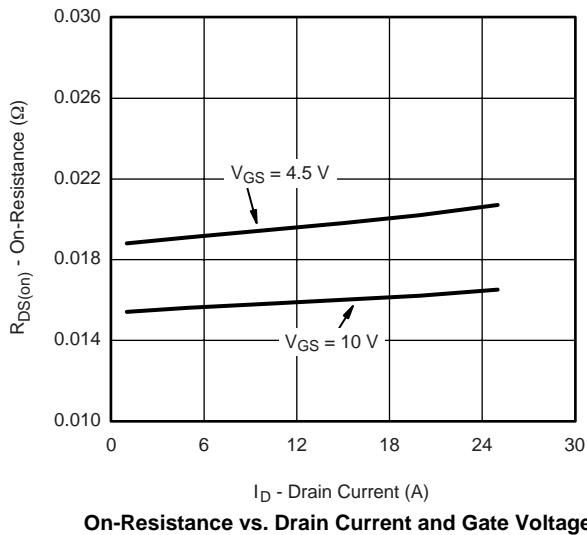
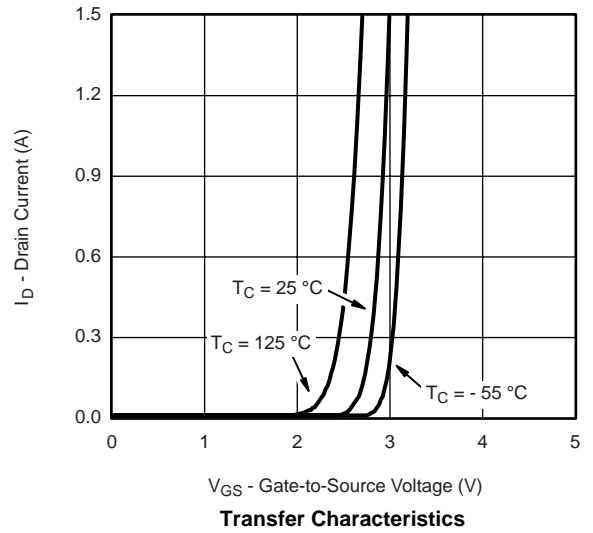
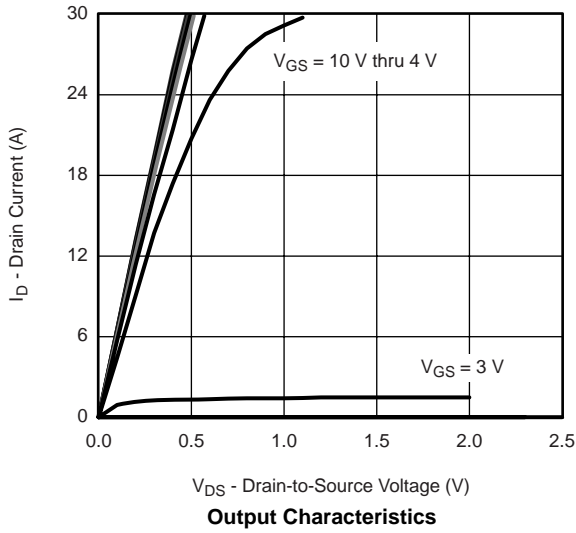
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted								
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit		
<b>Static</b>								
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V		
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		33		mV/°C		
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 6.2				
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		3	V		
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA		
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$		
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10			
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	20			A		
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$		0.016	0.032	$\Omega$		
		$V_{GS} = 4.5\text{ V}, I_D = 4\text{ A}$		0.029	0.045			
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 10\text{ V}, I_D = 5\text{ A}$		24		S		
<b>Dynamic<sup>b</sup></b>								
Input Capacitance	$C_{iss}$	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1295		pF		
Output Capacitance	$C_{oss}$			170				
Reverse Transfer Capacitance	$C_{rss}$			72				
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 5\text{ A}$		21.8	33	nC		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$		9.2	14			
Gate-Drain Charge	$Q_{gd}$			3.8				
Gate Resistance	$R_g$			2.5				
Turn-On Delay Time	$t_{d(on)}$	$f = 1\text{ MHz}$		2.4		$\Omega$		
Rise Time	$t_r$		$V_{DD} = 15\text{ V}, R_L = 3\text{ }\Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		21		40	ns
Turn-Off DelayTime	$t_{d(off)}$				14		25	
Fall Time	$t_f$				20		40	
Turn-On Delay Time	$t_{d(on)}$			9	18			
Rise Time	$t_r$			10	20			
Turn-Off DelayTime	$t_{d(off)}$			8	16			
Fall Time	$t_f$			21	35			
				8	16			
<b>Drain-Source Body Diode Characteristics</b>								
Continous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			2.7	A		
Pulse Diode Forward Current	$I_{SM}$				30			
Body Diode Voltage	$V_{SD}$	$I_S = 1.7\text{ A}, V_{GS} = 0\text{ V}$		0.77	1.2	V		
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 3\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		21	40	ns		
Body Diode Reverse Recovery Charge	$Q_{rr}$			15	30	nC		
Reverse Recovery Fall Time	$t_a$			13		ns		
Reverse Recovery Rise Time	$t_b$			8				

Notes:

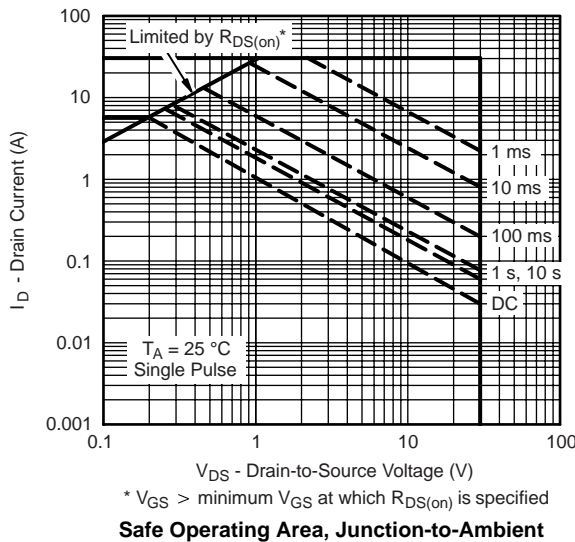
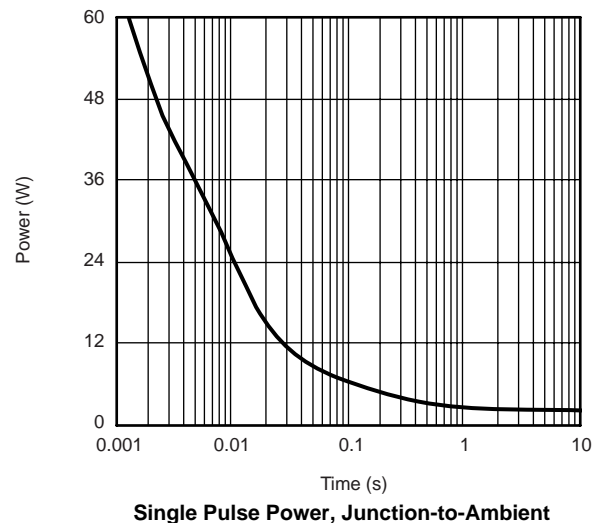
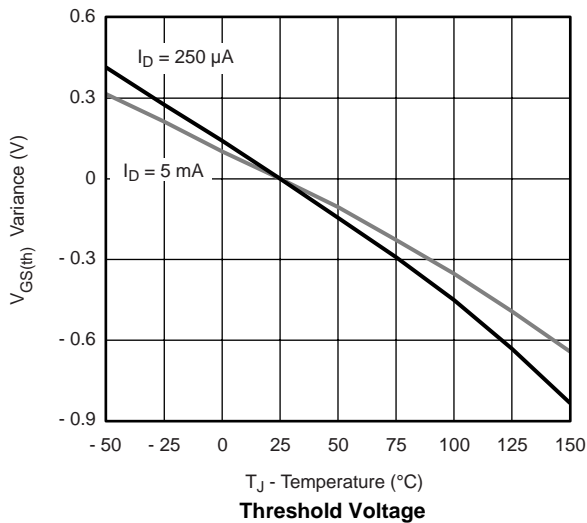
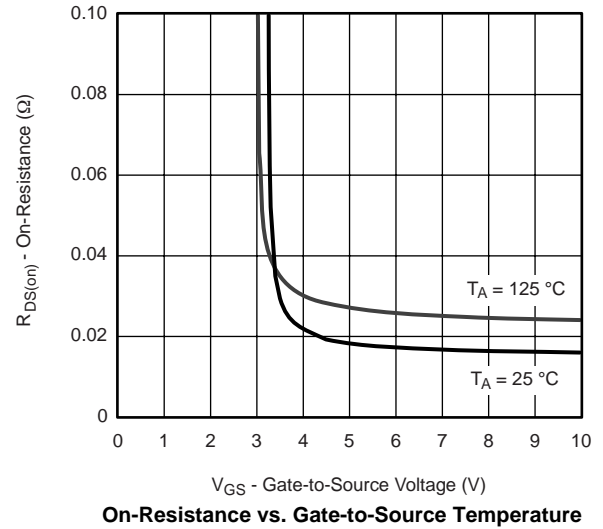
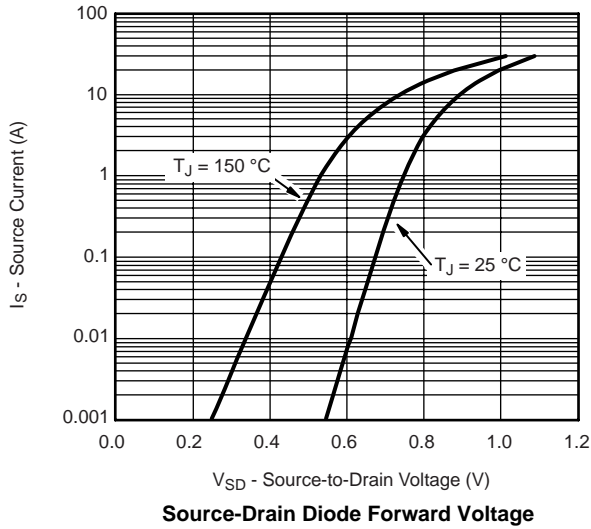
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

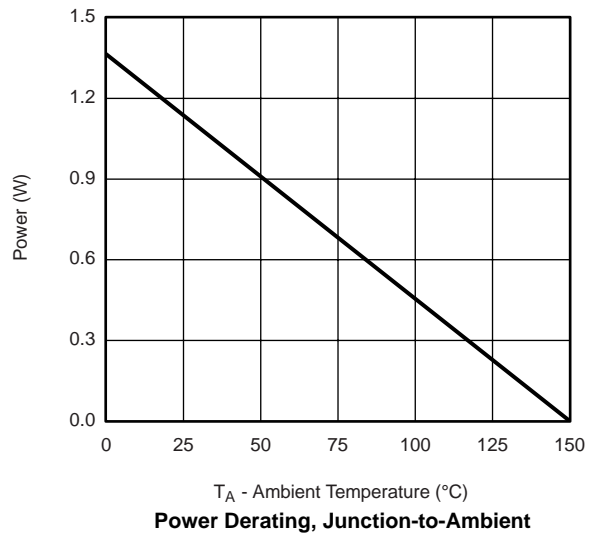
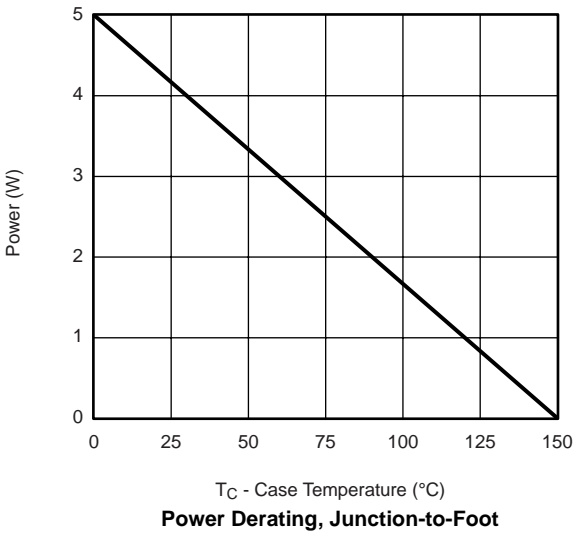
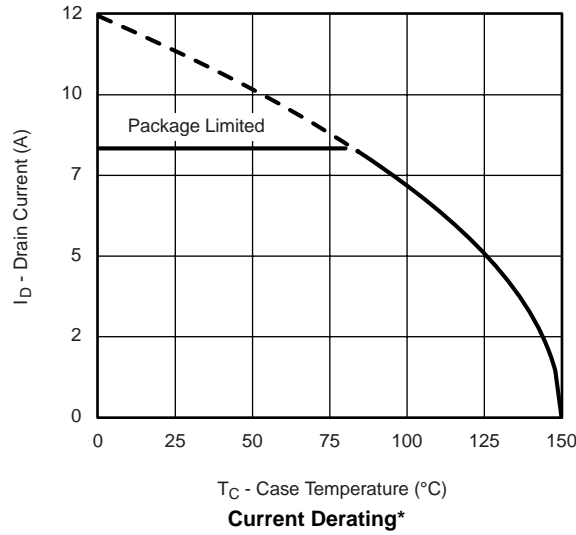
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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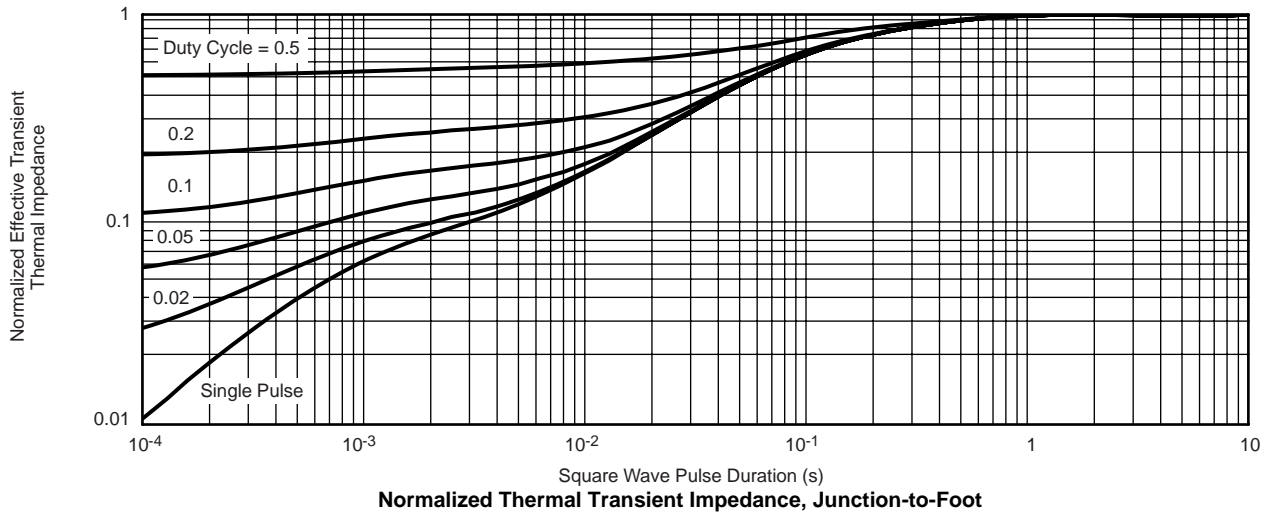
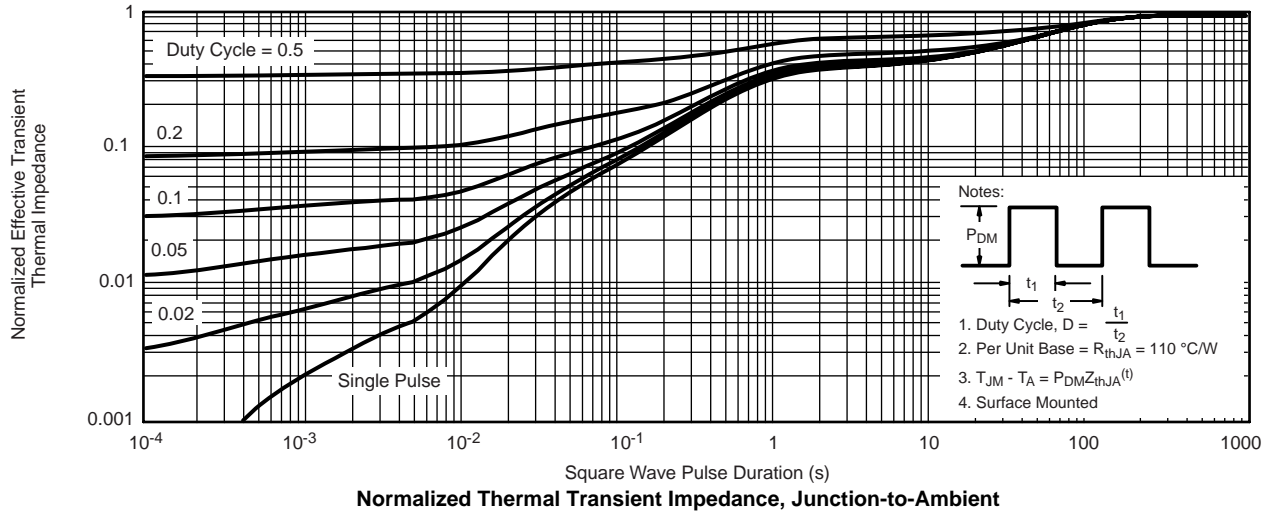


**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**SOIC (NARROW): 8-LEAD**

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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